Jorge M Garcia

List of Publications by Year
in descending order

169 papers	8,067 citations	57719 44 h-index	48277 88 g-index
173 all docs	173 docs citations	173 times ranked	4939 citing authors

#	Article	IF	Citations
1	Optical emission from a charge-tunable quantum ring. Nature, 2000, 405, 926-929.	13.7	832
2	Spectroscopy of Nanoscopic Semiconductor Rings. Physical Review Letters, 2000, 84, 2223-2226.	2.9	765
3	Intermixing and shape changes during the formation of InAs self-assembled quantum dots. Applied Physics Letters, 1997, 71, 2014-2016.	1.5	559
4	Production and processing of graphene and related materials. 2D Materials, 2020, 7, 022001.	2.0	333
5	Multiexciton Spectroscopy of a Single Self-Assembled Quantum Dot. Physical Review Letters, 1998, 80, 4991-4994.	2.9	329
6	Intersublevel transitions in InAs/GaAs quantum dots infrared photodetectors. Applied Physics Letters, 1998, 73, 2003-2005.	1.5	254
7	Nanometer-Scale Resolution of Strain and Interdiffusion in Self-AssembledInAs/GaAsQuantum Dots. Physical Review Letters, 2000, 85, 1694-1697.	2.9	203
8	In(Ga)As self-assembled quantum ring formation by molecular beam epitaxy. Applied Physics Letters, 2003, 82, 2401-2403.	1.5	195
9	Oscillatory Persistent Currents in Self-Assembled Quantum Rings. Physical Review Letters, 2007, 99, 146808.	2.9	192
10	Manipulating exciton fine structure in quantum dots with a lateral electric field. Applied Physics Letters, 2007, 90, 041101.	1.5	186
11	Electronic states tuning of InAs self-assembled quantum dots. Applied Physics Letters, 1998, 72, 3172-3174.	1.5	149
12	Giant permanent dipole moments of excitons in semiconductor nanostructures. Physical Review B, 2002, 65, .	1.1	147
13	Influence of buffer-layer surface morphology on the self-organized growth of InAs on InP(001) nanostructures. Applied Physics Letters, 2000, 76, 1104-1106.	1.5	133
14	Atomic-scale structure of self-assembled In(Ga)As quantum rings in GaAs. Applied Physics Letters, 2005, 87, 131902.	1.5	126
15	Fine Structure of Highly Charged Excitons in Semiconductor Quantum Dots. Physical Review Letters, 2003, 90, 247403.	2.9	124
16	Carrier-carrier correlations in an optically excited single semiconductor quantum dot. Physical Review B, 2000, 61, 11009-11020.	1.1	117
17	Hybridization of electronic states in quantum dots through photon emission. Nature, 2004, 427, 135-138.	13.7	113
18	Room temperature emission at 1.6Î¼m from InGaAs quantum dots capped with GaAsSb. Applied Physics Letters, 2005, 87, 202108.	1.5	106

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19	Formation of nanoscale ferromagnetic MnAs crystallites in low-temperature grown GaAs. Applied Physics Letters, 1997, 71, 2532-2534.	1.5	104
20	Strain relaxation and segregation effects during self-assembled InAs quantum dots formation on GaAs(001). Applied Physics Letters, 2000, 77, 409-411.	1.5	99
21	Graphene growth on h-BN by molecular beam epitaxy. Solid State Communications, 2012, 152, 975-978.	0.9	92
22	Photoluminescence up-conversion in InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2000, 77, 812-814.	1.5	91
23	Metallization-induced spontaneous silicide formation at room temperature: The Fe/Si case. Physical Review B, 1992, 46, 13339-13344.	1.1	90
24	Optical investigation of type II GaSbâˆ•GaAs self-assembled quantum dots. Applied Physics Letters, 2007, 91, .	1.5	86
25	Size quantization effects in InAs self-assembled quantum dots. Applied Physics Letters, 1997, 70, 1727-1729.	1.5	82
26	Excitons in self-assembled quantum ring-like structures. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 510-513.	1.3	82
27	InAs/InP(001) quantum wire formation due to anisotropic stress relaxation: in situ stress measurements. Journal of Crystal Growth, 2001, 227-228, 975-979.	0.7	77
28	Growth and Electronic Properties of Self-Organized Quantum Rings. Japanese Journal of Applied Physics, 2001, 40, 1857-1859.	0.8	74
29	Lateral confinement of surface states on stepped Cu(111). Physical Review B, 1995, 52, 7894-7897.	1.1	73
30	Laser devices with stacked layers of InGaAs/GaAs quantum rings. Nanotechnology, 2004, 15, S126-S130.	1.3	71
31	Vertical order in stacked layers of self-assembled In(Ga)As quantum rings on GaAs (001). Applied Physics Letters, 2005, 86, 071918.	1.5	71
32	Optical transitions and excitonic recombination in InAs/InP self-assembled quantum wires. Applied Physics Letters, 2001, 78, 4025-4027.	1.5	65
33	Absorption and photoluminescence spectroscopy on a single self-assembled charge-tunable quantum dot. Physical Review B, 2005, 72, .	1.1	65
34	Magneto-optical properties of charged excitons in quantum dots. Physical Review B, 2002, 66, .	1.1	63
35	Oscillator strength reduction induced by external electric fields in self-assembled quantum dots and rings. Physical Review B, 2007, 75, .	1.1	60
36	Fe thin-film growth on Au(100): A self-surfactant effect and its limitations. Physical Review B, 1999, 59, 15966-15974.	1.1	58

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37	Giant magnetoresistance in a low-temperature GaAs/MnAs nanoscale ferromagnet hybrid structure. Applied Physics Letters, 1998, 73, 3291-3293.	1.5	57
38	Multilayer graphene grown by precipitation upon cooling of nickel on diamond. Carbon, 2011, 49, 1006-1012.	5.4	56
39	Morphological transformation of InyGa1â[^]'yAs islands, fabricated by Stranskiâ€"Krastanov growth. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 225-229.	1.7	52
40	Temperature-dependent linewidth of charged excitons in semiconductor quantum dots: Strongly broadened ground state transitions due to acoustic phonon scattering. Physical Review B, 2004, 69, .	1.1	47
41	Continuum and discrete excitation spectrum of single quantum rings. Physical Review B, 2005, 72, .	1.1	47
42	Carrier recombination effects in strain compensated quantum dot stacks embedded in solar cells. Applied Physics Letters, 2008, 93, 123114.	1.5	46
43	Magneto-optical properties of ring-shaped self-assembled InGaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 165-169.	1.3	45
44	Interdependence of strain and shape in self-assembled coherent InAs islands on GaAs. Europhysics Letters, 1999, 45, 222-227.	0.7	44
45	Electron wave-function spillover in self-assembledInAsâ^•InPquantum wires. Physical Review B, 2004, 70, .	1.1	44
46	Charging dynamics of InAs self-assembled quantum dots. Physical Review B, 1997, 56, 3609-3612.	1.1	43
47	Luminescence quenching in InAs quantum dots. Applied Physics Letters, 2001, 78, 2946-2948.	1.5	39
48	Effect of an additional infrared excitation on the luminescence efficiency of a single InAs/GaAs quantum dot. Physical Review B, 2003, 68, .	1.1	37
49	Optical coupling of two distant InAs/GaAs quantum dots by a photonic-crystal microcavity. Physical Review B, 2010, 81, .	1.1	37
50	Ordered InAs quantum dots on pre-patterned GaAs (001) by local oxidation nanolithography. Journal of Crystal Growth, 2005, 284, 313-318.	0.7	36
51	Multilayer graphene films grown by molecular beam deposition. Solid State Communications, 2010, 150, 809-811.	0.9	35
52	Molecular beam growth of graphene nanocrystals on dielectric substrates. Carbon, 2012, 50, 4822-4829.	5.4	34
53	Influence of excitation energy on charged exciton formation in self-assembled InAs single quantum dots. Physical Review B, 2001, 64, .	1.1	33
54	Excitonic behavior in self-assembled InAs/GaAs quantum rings in high magnetic fields. Physical Review B, 2009, 80, .	1.1	33

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55	Temperature influence on optical charging of self-assembled InAs/GaAs semiconductor quantum dots. Applied Physics Letters, 2001, 78, 2952-2954.	1.5	32
56	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. Journal of Crystal Growth, 2003, 251, 155-160.	0.7	32
57	Enhancement of the room temperature luminescence of InAs quantum dots by GaSb capping. Applied Physics Letters, 2007, 91, .	1.5	31
58	A robust machine learning framework to identify signatures for frailty: a nested case-control study in four aging European cohorts. GeroScience, 2021, 43, 1317-1329.	2.1	31
59	Magnetoluminescence of highly excited InAs/GaAs self-assembled quantum dots. Physical Review B, 2000, 62, 7344-7349.	1.1	30
60	Grazing-incidence diffraction anomalous fine structure of InAs/InP(001) self-assembled quantum wires. Europhysics Letters, 2002, 57, 499-505.	0.7	28
61	Optical emission from single, charge-tunable quantum rings. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 9, 124-130.	1.3	27
62	Atomic-scale structure and formation of self-assembled In(Ga)As quantum rings. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 41-45.	1.3	27
63	Magnetoplasmonic Nanorings as Novel Architectures with Tunable Magnetoâ€optical Activity in Wide Wavelength Ranges. Advanced Optical Materials, 2014, 2, 612-617.	3.6	27
64	Graphene growth on Pt(111) and Au(111) using a MBE carbon solid-source. Diamond and Related Materials, 2015, 57, 58-62.	1.8	27
65	Size-filtering effects by stacking InAs/InP (001) self-assembled quantum wires into multilayers. Physical Review B, 2002, 65, .	1.1	25
66	Electronic structure of nanometer-size quantum dots and quantum rings. Microelectronic Engineering, 1999, 47, 95-99.	1.1	24
67	Acceptor-induced threshold energy for the optical charging of InAs single quantum dots. Physical Review B, 2002, 66, .	1.1	24
68	Scanning tunnelling microscopy and spectroscopy on organic PTCDA films deposited on sulfur passivated GaAs(001). Journal of Physics Condensed Matter, 2003, 15, S2619-S2629.	0.7	24
69	Stress evolution aspects during InAs/InP (001) quantum wires self-assembling. Microelectronics Journal, 2004, 35, 13-17.	1.1	21
70	Isolated self-assembled InAs/InP(001) quantum wires obtained by controlling the growth front evolution. Nanotechnology, 2007, 18, 035604.	1.3	21
71	Surface stress effects during MBE growth of IIIâ€"V semiconductor nanostructures. Journal of Crystal Growth, 2001, 227-228, 995-999.	0.7	20
72	In situ measurements of As/P exchange during InAs/InP(0 0 1) quantum wires growth. Applied Surface Science, 2002, 188, 188-192.	3.1	20

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73	Formation of the charged exciton complexes in self-assembled InAs single quantum dots. Journal of Applied Physics, 2002, 92, 6787-6793.	1.1	19
74	Tuning of electronic states in self-assembled InAs quantum dots using an ion implantation technique. Journal of Electronic Materials, 1998, 27, 1030-1033.	1.0	17
75	Customized nanostructures MBE growth: from quantum dots to quantum rings. Journal of Crystal Growth, 2003, 251, 213-217.	0.7	17
76	Emission polarization control in semiconductor quantum dots coupled to a photonic crystal microcavity. Optics Express, 2010, 18, 13301.	1.7	17
77	CFTS-3/In2S3/SnO2:F heterojunction structure as eco-friendly photocatalytic candidate for removing organic pollutants. Arabian Journal of Chemistry, 2020, 13, 6366-6378.	2.3	16
78	Auger processes in InAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 440-443.	1.3	15
79	In segregation effects during quantum dot and quantum ring formation on GaAs(001). Microelectronics Journal, 2004, 35, 7-11.	1.1	15
80	Determination of the energy levels on InAs quantum dots with respect to the GaAs conduction band. Nanotechnology, 2005, 16, S282-S284.	1.3	15
81	Physical properties investigation and gas sensing mechanism of Al: Fe2O3 thin films deposited by spray pyrolysis. Superlattices and Microstructures, 2019, 129, 91-104.	1.4	15
82	Strain-induced optical anisotropy in self-organized quantum structures at the E1 transition. Applied Physics Letters, 2000, 76, 2197-2199.	1.5	14
83	Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots. Physical Review B, 2010, 82, .	1.1	14
84	Three dimensional atom probe imaging of GaAsSb quantum rings. Ultramicroscopy, 2011, 111, 1073-1076.	0.8	14
85	Growth of epitaxial iron disilicide on Si(100). Surface Science, 1992, 269-270, 1016-1021.	0.8	13
86	Optical Properties of Semiconductor Nanostructures. , 2000, , .		13
87	Excited states of ring-shaped (InGa)As quantum dots in aGaAsâˆ•(AlGa)Asquantum well. Physical Review B, 2005, 72, .	1.1	13
88	Lateral carrier tunnelling in stacked In(Ga)As/GaAs quantum rings. European Physical Journal B, 2006, 54, 217-223.	0.6	13
89	Single- and bi-layer graphene grown on sapphire by molecular beam epitaxy. Solid State Communications, 2014, 189, 15-20.	0.9	13
90	Single-photon emission by semiconductor quantum rings in a photonic crystal. Journal of the Optical Society of America B: Optical Physics, 2010, 27, A21.	0.9	12

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91	Exceptionally large migration length of carbon and topographically-facilitated self-limiting molecular beam epitaxial growth of graphene on hexagonal boron nitride. Carbon, 2017, 114, 579-584.	5.4	12
92	Growth of the next generation promising Cu2 Fe1-xCoxSnS4 thin films and efficient p-CCTS/n-In2S3/n-SnO2F heterojunction for optoelectronic applications. Materials Research Bulletin, 2021, 133, 111028.	2.7	12
93	Straindashinduced enhanced solubility of Au in epitaxial films of Fe. Surface Science, 1996, 364, L505-L510.	0.8	11
94	Epitaxial metallic nanostructures on GaAs. Surface Science, 2001, 482-485, 910-915.	0.8	11
95	Shape dependent electronic structure and exciton dynamics in small In(Ga)As quantum dots. European Physical Journal B, 2006, 54, 471-477.	0.6	11
96	Preparation and passivation of GaAs(001) surfaces for growing organic molecules. Nanotechnology, 2002, 13, 352-356.	1.3	10
97	Emission from neutral and charged excitons in a single quantum dot in a magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 184-188.	1.3	10
98	Effect of carrier transfer on the PL intensity in self-assembled In (Ga) As/GaAs quantum rings. EPJ Applied Physics, 2006, 35, 159-163.	0.3	10
99	Self-assembled InAs quantum wire lasers on (001)InP at 1.6Î¼m. Applied Physics Letters, 2006, 89, 091123.	1.5	10
100	Epitaxial CuInSe2 thin films grown by molecular beam epitaxy and migration enhanced epitaxy. Journal of Crystal Growth, 2017, 475, 300-306.	0.7	10
101	System for manufacturing complete Cu(In,Ga)Se2 solar cells in situ under vacuum. Solar Energy, 2020, 198, 490-498.	2.9	10
102	Limited In incorporation during pseudomorphic InAs/GaAs growth and quantum dot formation observed by in situ stress measurements. Applied Surface Science, 2002, 188, 75-79.	3.1	9
103	A successful exploitation of gamma-radiation on chalcogenide Cu2InSnS4 towards clean water under photocatalysis approach. Journal of Molecular Structure, 2022, 1251, 131943.	1.8	9
104	Synthesis of new promising quaternary Cu2InSnS4 absorber layer: Physical behaviors, wettability and photocatalysis applications. Journal of Alloys and Compounds, 2022, 898, 162771.	2.8	9
105	Glancing-angle diffraction anomalous fine structure of InAs quantum dots and quantum wires. Journal of Synchrotron Radiation, 2001, 8, 536-538.	1.0	8
106	Optical Up-Conversion Processes in InAs Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 2080-2083.	0.8	8
107	Glancing angle EXAFS of encapsulated self-assembled InAs/InP quantum wires and InAs/GaAs quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 174-180.	1.7	8
108	Vertical stacks of small InAs/GaAs self-assembled dots: resonant and non-resonant excitation. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 46-49.	1.3	8

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109	Competence of tunable Cu2AlSnS4 chalcogenides hydrophilicity toward high efficacy photodegradation of spiramycin antibiotic resistance-bacteria from wastewater under visible light irradiation. Journal of Photochemistry and Photobiology A: Chemistry, 2022, 431, 114041.	2.0	8
110	Field dependent carrier dynamics and charged excitons in InAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 627-631.	1.3	7
111	Charged excitons in individual quantum dots: effects of vertical electric fields and optical pump power. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 35-36.	1.3	7
112	Giant V oc Boost of Lowâ€Temperature Annealed Cu(In,Ga)Se 2 with Sputtered Zn(O,S) Buffers. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900145.	1.2	6
113	Modeling of the Magnetization Behavior of Realistic Self-Organized InAs/GaAs Quantum Craters as Observed with Cross-Sectional STM. AIP Conference Proceedings, 2005, , .	0.3	5
114	Surface characterization of IIIâ€"V heteroepitaxial systems by laser light scattering. Journal of Crystal Growth, 1999, 201-202, 137-140.	0.7	4
115	Magnetic properties of charged excitons in self-assembled quantum dots. Physica Status Solidi (B): Basic Research, 2003, 238, 293-296.	0.7	4
116	Magneto-excitonic states in charge-tunable self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 233-241.	1.3	4
117	Theoretical modelling of quaternary GaInAsSb/GaAs self-assembled quantum dots. Journal of Physics: Conference Series, 2010, 245, 012081.	0.3	4
118	First principal investigation of structural, morphological, optoelectronic and magnetic characteristics of sprayed Zn: Fe2O3 thin films. Optik, 2020, 219, 165303.	1.4	4
119	Optical spectroscopy of a single self-assembled quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 694-700.	1.3	3
120	Optical Properties of Self-Assembled GaxIn1-xAs/InP Quantum Wires. Physica Status Solidi A, 2002, 190, 763-768.	1.7	3
121	Grazing incidence diffraction anomalous fine structure of self-assembled semiconductor nanostructures. Nuclear Instruments & Methods in Physics Research B, 2003, 200, 24-33.	0.6	3
122	Size self-filtering effect in vertical stacks of InAs/InP self-assembled quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 174-176.	1.3	3
123	Grazing incidence diffraction anomalous fine structure: a tool for investigating strain distribution and interdiffusion in InAs/InP quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 541-542.	1.3	3
124	Confinement in self-assembled InAs/InP quantum wires studied by magneto-photoluminescence. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 261-264.	1.3	3
125	Strain determination in MBE-grownInAsquantum wires onInP. Physical Review B, 2006, 73, .	1.1	3
126	Competition between carrier recombination and tunneling in quantum dots and rings under the action of electric fields. Superlattices and Microstructures, 2008, 43, 582-587.	1.4	3

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127	Counting molecular-beam grown graphene layers. Applied Physics Letters, 2013, 102, 241905.	1.5	3
128	Confining surface state electrons in less than two dimensions: A spectroscopic study. Applied Physics A: Materials Science and Processing, 1995, 61, 609-613.	1.1	3
129	Carrier Recombination in InAs/GaAs Self-Assembled Quantum Dots under Resonant Excitation Conditions. Physica Status Solidi A, 2002, 190, 583-587.	1.7	2
130	Exciton Recombination in Self-Assembled InAs/GaAs Small Quantum Dots under an External Electric Field. Physica Status Solidi A, 2002, 190, 599-603.	1.7	2
131	The influence of carrier diffusion on the formation of charged excitons in InAs/GaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 101-104.	1.3	2
132	Size filtering effect in vertical stacks of In(Ga)As/GaAs self-assembled quantum rings. Materials Science and Engineering C, 2006, 26, 297-299.	3.8	2
133	Modulation spectroscopy on a single self assembled quantum dot. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 381-389.	0.8	2
134	Carrier Diffusion in the Barrier Enabling Formation of Charged Excitons in InAs/GaAs Quantum Dots. Acta Physica Polonica A, 2001, 100, 387-395.	0.2	2
135	A structural characterization of the buffer layer for growth of magnetically coupled Co/Cu superlattices. Journal of Magnetism and Magnetic Materials, 1993, 121, 20-23.	1.0	1
136	A growth method to obtain flat and relaxed In0.2Ga0.8As on GaAs (001) developed through in situ monitoring of surface topography and stress evolution. Journal of Crystal Growth, 2001, 227-228, 36-40.	0.7	1
137	Charged Excitons in Self-assembled Quantum Dots. Materials Research Society Symposia Proceedings, 2002, 737, 75.	0.1	1
138	Influence of the InAs coverage on the phonon-assisted recombination in InAs/GaAs quantum dots. Surface Science, 2002, 507-510, 624-629.	0.8	1
139	Optical emission of InAs/GaAs quantum rings coupled to a two-dimensional photonic crystal microcavity. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2156-2159.	1.3	1
140	Temperature dependent optical properties of stacked InGaAs/GaAs quantum rings. Materials Science and Engineering C, 2008, 28, 887-890.	3.8	1
141	Single photon emission and quantum ring-cavity coupling in InAs/GaAs quantum rings. Journal of Physics: Conference Series, 2010, 210, 012037.	0.3	1
142	0D Band Gap Engineering by MBE Quantum Rings: Fabrication and Optical Properties. Nanoscience and Technology, 2014, , 61-82.	1.5	1
143	Exploration of spray pyrolysis technique in preparation of absorber material CFATS: Unprecedented hydrophilic surface and antibacterial properties. Arabian Journal of Chemistry, 2022, 15, 103894.	2.3	1
144	Formation and Properties of Nanosize Ferromagnetic MnAs Particles in Low Temperature GaAs by Manganese Implantation. Materials Research Society Symposia Proceedings, 1997, 475, 49.	0.1	0

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145	Strain and Shape in Self-Assembled Quantum Dots Studied by X-Ray Grazing Incidence Diffraction. Materials Research Society Symposia Proceedings, 1998, 524, 89.	0.1	0
146	Optical Spectroscopy of Single Self Assembled Quantum Dots. Materials Research Society Symposia Proceedings, 1999, 571, 135.	0.1	0
147	Critical size for localization of the L-like conduction states in InAs quantum dots grown on GaAs. Applied Physics Letters, 2000, 76, 2919-2921.	1.5	0
148	Excited-State Magnetoluminescence of InAs/GaAs Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 1998-2001.	0.8	0
149	Optical Charging of Self-Assembled InAs/GaAs Quantum Dots. Physica Scripta, 2002, T101, 140.	1.2	0
150	Effective tuning of the charge-state of single In(Ga)As/GaAs quantum dots by below barrier band gap excitation. Surface Science, 2003, 532-535, 843-847.	0.8	0
151	Pure luminescence transitions from a small InAs/GaAs quantum dot exhibiting a single electron level. , 0, , .		0
152	Fine structure of highly charged quantum dot excitons: turning dark into bright states. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 421-425.	0.8	0
153	Temperature study of the photoluminescence of a single InAs/GaAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 608-611.	0.8	0
154	Electronic quantum dot states induced through photon emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2079-2093.	0.8	0
155	Luminescence and photocurrent spectroscopy of self-assembled InAs quantum wires on InP[001]. , 0, , .		0
156	Magnetotunneling spectroscopy of ring-shaped (InGa)As quantum dots: Evidence of excited states with 2pz character. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 57-60.	1.3	0
157	Enhancement of the photoluminescence intensity of a single InAs/GaAs quantum dot by separate generation of electrons and holes. Physics of the Solid State, 2006, 48, 1993-1999.	0.2	0
158	Electro-Optical Characterization of Self-Assembled InAs/GaAs Quantum Rings Embedded in P-i-N and Schottky Diodes. AIP Conference Proceedings, 2007, , .	0.3	0
159	Near Room Temperature InAs Quantum Wires Lasers on InP at Short Wavelength Infrared. , 2007, , .		0
160	Oscillatory persistent currents in nano-volcanoes. AIP Conference Proceedings, 2007, , .	0.3	0
161	(InP)5/(Ga0.47In0.53As)4 short-period superlattices waveguides for InAs quantum wires lasers. Journal of Crystal Growth, 2007, 306, 16-21.	0.7	0
162	Publisher's Note: Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots [Phys. Rev. B82, 235316 (2010)]. Physical Review B, 2010, 82, .	1.1	0

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163	Microcavity-Mediated Coupling of Two Distant InAsâˆ•GaAs Quantum Dots. , 2011, , .		0
164	Magnetoplasmonics: Magnetoplasmonic Nanorings as Novel Architectures with Tunable Magnetoâ€optical Activity in Wide Wavelength Ranges (Advanced Optical Materials 7/2014). Advanced Optical Materials, 2014, 2, 600-600.	3.6	0
165	Circularly Polarized Emission from Ensembles of InGaAs/GaAs Quantum Rings. Silicon, 2017, 9, 689-693.	1.8	0
166	Optimization of a carbon evaporator cell for MBE growth. Vacuum, 2020, 181, 109653.	1.6	0
167	Interband Optics of Charge-Tunable Quantum Dots. , 2000, , 347-363.		0
168	Scanning tunneling spectroscopic monitoring of surface states role on water passivation of InGaAs uncapped quantum dots. RSC Advances, 2017, 7, 33137-33142.	1.7	0
169	Chemical composition and strain distribution of InAs/GaAs(001) stacked quantum rings. , 0, , 271-274.		0